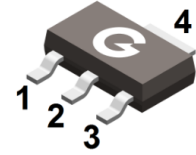
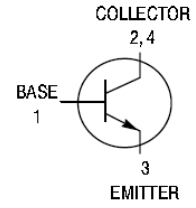


Features

- Epitaxial planar die construction
- Complimentary to PZT2907A
- Ideal for low power amplification and switching
- RoHS compliant with Halogen-free

HF



SOT-223

Mechanical Data

- Case: SOT-223
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
PZT2222A	SOT-223	4000 pcs / Tape & Reel	1P

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	75	V
Collector-Emitter Breakdown Voltage	V _{CEO}	40	V
Emitter-Base Breakdown Voltage	V _{EBO}	6	V
Collector Current (Continuous)	I _C	0.6	A
Collector Current –Peak pulse width ≤ 40μs, δ = 0.35	I _{CM}	1.5	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (T _A = 25°C)	P _D	2	W
Thermal Resistance Junction-to-Air *1	R _{θJA}	60	°C/W
Thermal Resistance Junction-to-Case *1	R _{θJC}	25	°C/W
Thermal Resistance Junction-to-Lead *1	R _{θJL}	15	°C/W
Ambient Temperature	T _A	-55 ~ +150	°C
Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Note 1: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	75	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	6	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 60\text{V}, I_E = 0$	-	-	10	nA
Collector Cut-off Current	I_{CEX}	$V_{CE} = 60\text{V}, V_{EB(OFF)} = 3\text{V}$	-	-	10	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$	-	-	10	nA
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 0.1\text{mA}$	35	-	-	-
		$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	50	-	-	-
		$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	75	-	-	-
		$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	100	-	300	-
		$V_{CE} = 10\text{V}, I_C = 500\text{mA}$	40	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$	-	-	0.3	V
		$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	1	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$	-	-	1.2	V
		$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	2	V
Base-Emitter Voltage	$V_{BE(on)}$	$I_C = 200\text{mA}, V_{CE} = 10\text{V}$	-	-	1	V
Transition Frequency	f_T	$I_C = 20\text{mA}, V_{CE} = 20\text{V}$ $f = 100\text{MHz}$	300	-	-	MHz
Collector Output Capacitance	C_{OBO}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	-	-	8	pF
Noise Figure	N_F	$V_{CE} = 10\text{V}, I_C = 100\mu\text{A}$ $R_S = 1.0\text{K}\Omega, f = 1.0\text{kHz}$	-	-	4.0	dB
Delay Time	t_d	$V_{CC} = 30\text{V}, I_C = 150\text{mA}$	-	-	10	ns
Rise Time	t_r	$V_{BE(OFF)} = -0.5\text{V}, I_{B1} = 15\text{mA}$	-	-	25	ns
Storage Time	t_s	$V_{CC} = 30\text{V}, I_C = 150\text{mA}$	-	-	225	ns
Fall Time	t_f	$I_{B1} = I_{B2} = 15\text{mA}$	-	-	60	ns

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

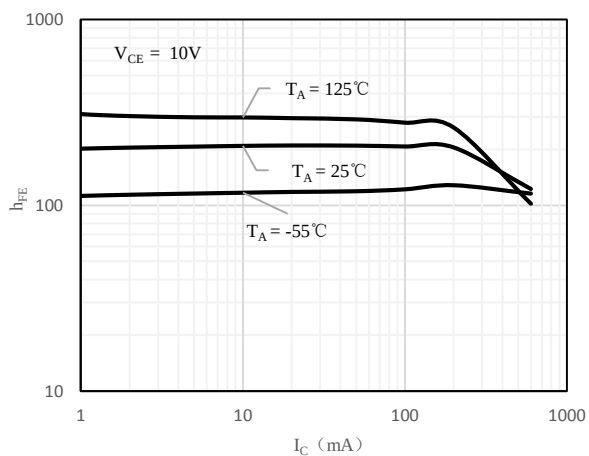


Fig 1 h_{FE} vs. I_C

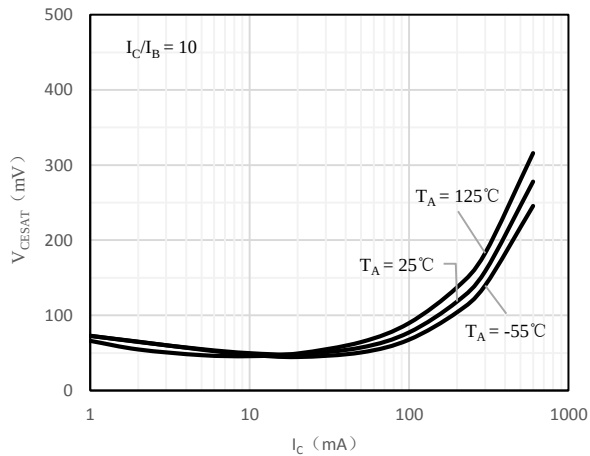


Fig 2 $V_{CE(sat)}$ vs. I_C

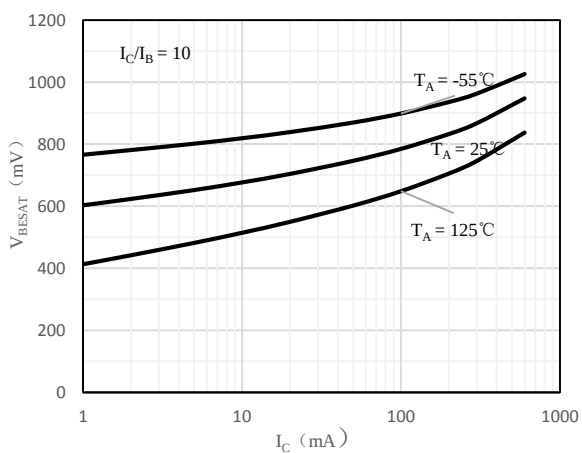


Fig 3 $V_{BE(sat)}$ vs. I_C

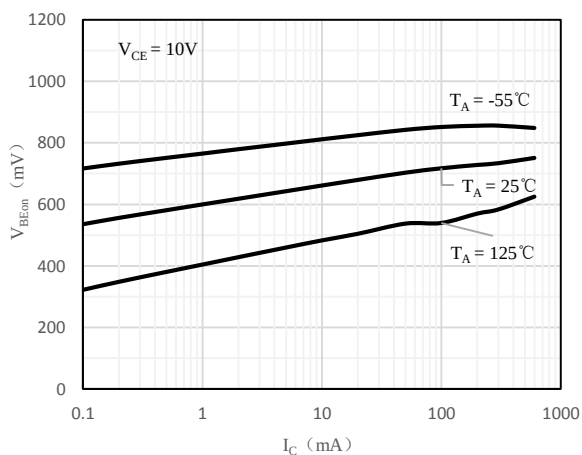


Fig 4 $V_{BE(on)}$ vs. I_C

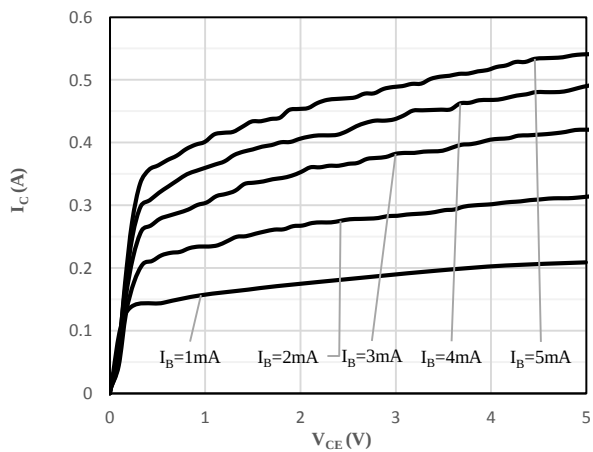


Fig 5 I_C vs. V_{CE}

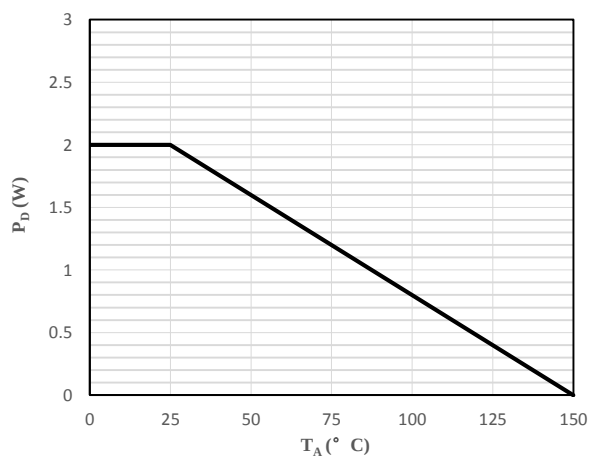


Fig 6 P_D vs. T_A

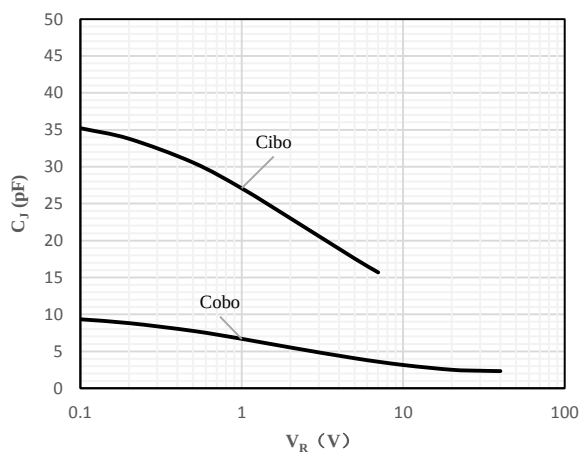
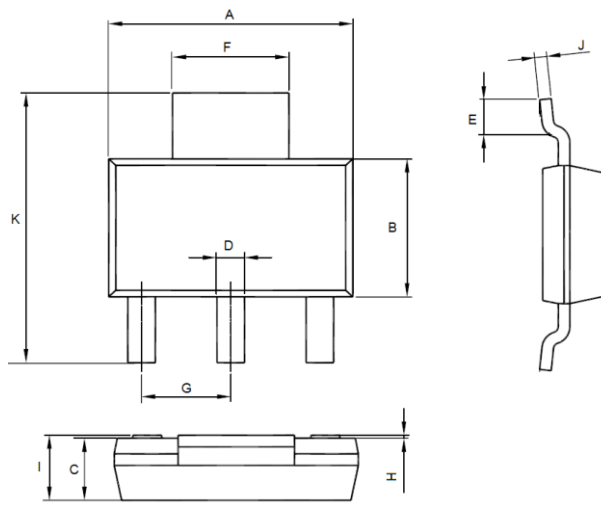


Fig 7 C_J vs. V_R

Package Outline Dimensions (Unit: mm)



SOT-223		
Dimension	Min.	Max.
A	6.10	6.50
B	3.30	3.70
C	1.50	1.70
D	0.66	0.82
E	0.90	1.15
F	2.90	3.10
G	2.20	2.40
H	0.02	0.10
I	1.52	1.80
J	0.20	0.40
K	6.70	7.30

Mounting Pad Layout (Unit: mm)

SOT-223

